

P-Channel 20-V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 20	0.035 at V _{GS} = - 10 V	- 5 ^e	10 nC
	0.043 at V _{GS} = - 4.5 V	- 5 ^e	
	0.061 at V _{GS} = - 2.5 V	- 4.8	

FEATURES

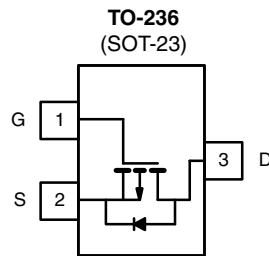
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch
- PA Switch
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 20	V
Gate-Source Voltage	V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 5 ^e
		T _C = 70 °C	- 4.8
		T _A = 25 °C	- 4.5 ^{b, c}
		T _A = 70 °C	- 3.5 ^{b, c}
Pulsed Drain Current	I _{DM}	- 18	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 1.0 ^{b, c}
Maximum Power Dissipation	P _D	T _C = 25 °C	2.5
		T _C = 70 °C	1.6
		T _A = 25 °C	1.25 ^{b, c}
		T _A = 70 °C	0.8 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	75	100	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50		

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 166 °C/W.
- Package limited.



MOSFET SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 13.4		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.9		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.5		- 1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 18			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5.1 A		0.035		Ω
		V _{GS} = - 4.5 V, I _D = - 4.5 A		0.043		
		V _{GS} = - 2.5 V, I _D = - 3.7 A		0.061		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 5 V, I _D = - 5.1 A		15		S
Dynamic^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		835		pF
Output Capacitance	C _{oss}			180		
Reverse Transfer Capacitance	C _{rss}			155		
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 5.1 A		10		nC
				6.4		
Gate-Source Charge	Q _{gs}	V _{DS} = - 10 V, V _{GS} = - 2.5 V, I _D = - 5.1 A		1.7		
Gate-Drain Charge	Q _{gd}			3.4		
Gate Resistance	R _g	f = 1 MHz	0.9	4.4	8.8	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 2.4 Ω I _D = - 4.1 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		22	33	ns
Rise Time	t _r			20	30	
Turn-Off Delay Time	t _{d(off)}			28	42	
Fall Time	t _f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 2.1	A
Pulse Diode Forward Current ^a	I _{SM}				- 20	
Body Diode Voltage	V _{SD}	I _S = - 4.1 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 4.1 A, di/dt = 100 A/μs, T _J = 25 °C		23	35	ns
Body Diode Reverse Recovery Charge	Q _{rr}			12	20	nC
Reverse Recovery Fall Time	t _a			15		ns
Reverse Recovery Rise Time	t _b			8		

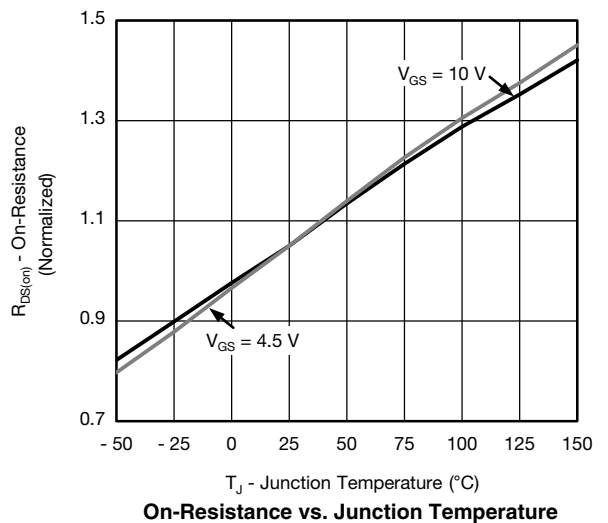
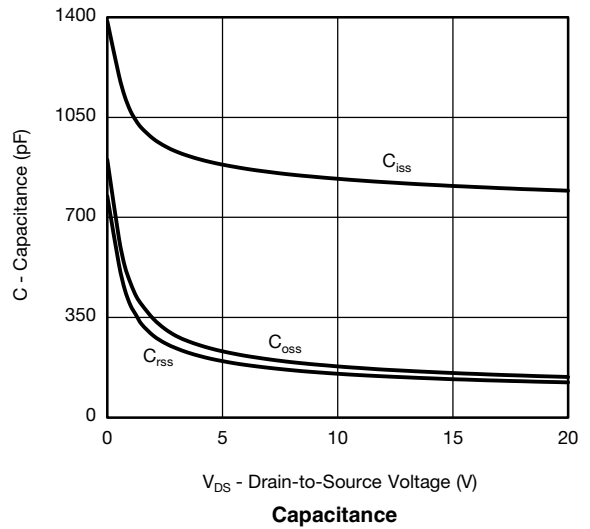
Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

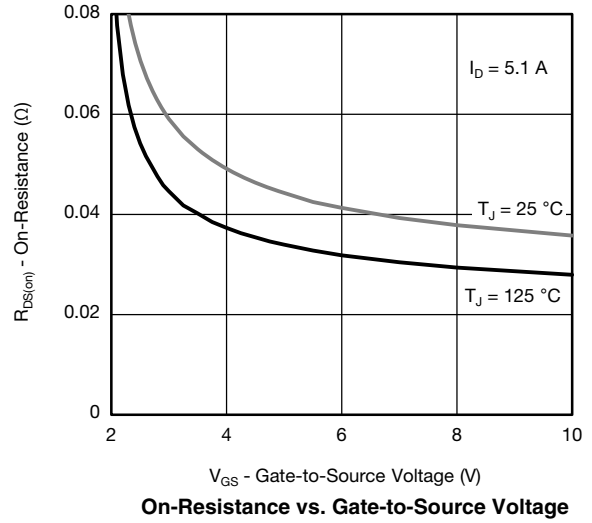
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



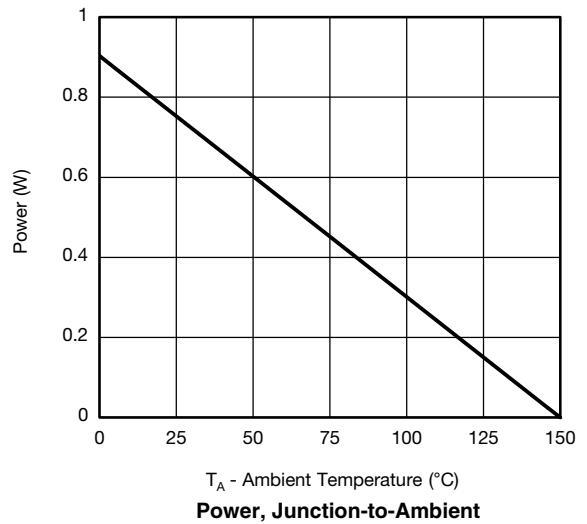
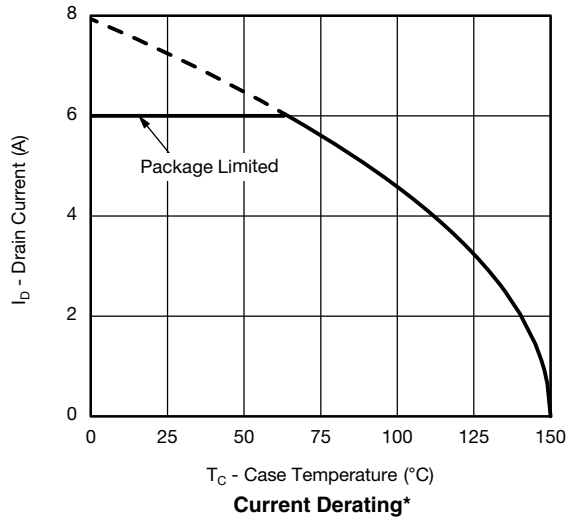
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



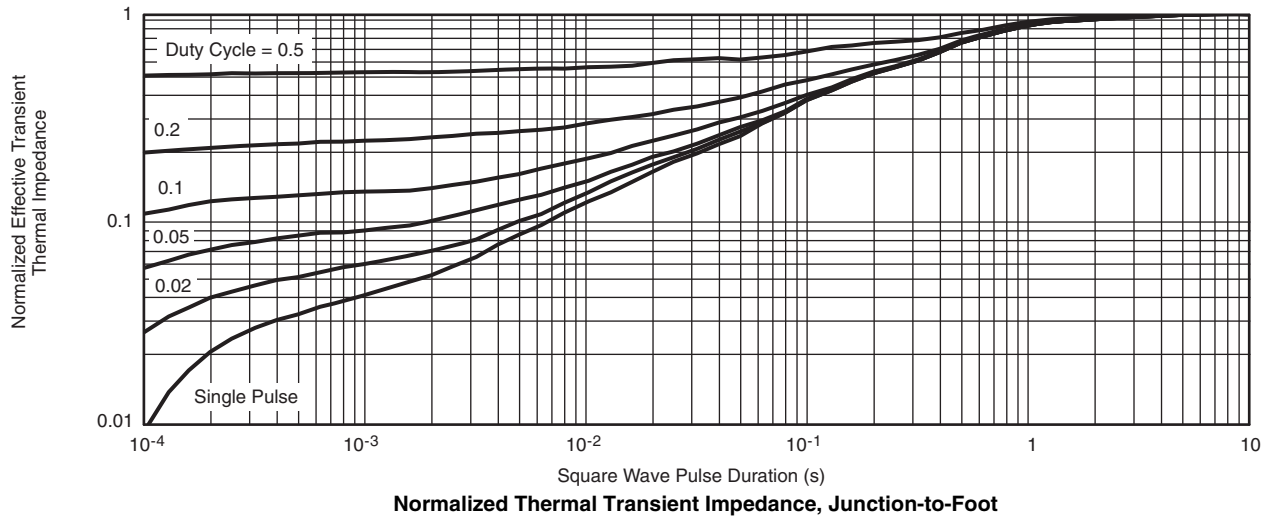
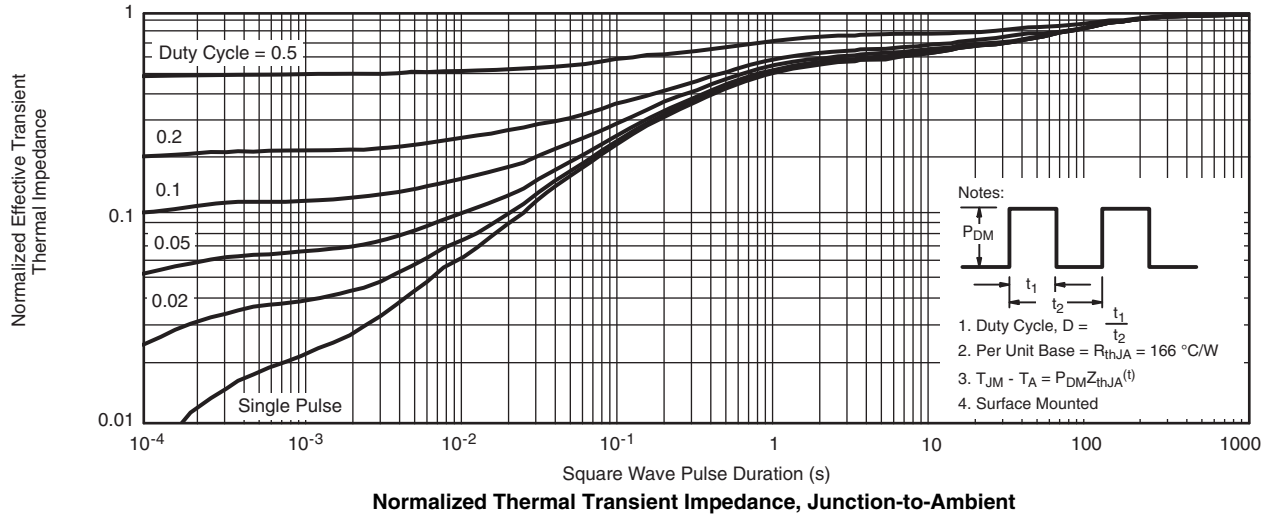
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)

